

SiC & GaN Power Component News

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2022:

[Boost Converter Demo Board Shows Off Benefits Of Controller & GaN FETs Combo](#), Efficient Power Conversion's EPC9166 demo board, How2Power Today, January 2022 issue.

[Third-Gen SiC MOSFETs Enhance Performance For EVs](#), STMicroelectronics' third-generation STPOWER SiC MOSFETs, How2Power Today, January 2022 issue.

2021:

[SiC Power Stage Reference Design Accelerates Inverter Development](#), Mersen's 150-kVA three-phase SiC Power Stack reference design developed in collaboration with Microchip Technology, How2Power Today, December 2021 issue.

[GaN Power ICs Integrate Fast Overcurrent And Overtemperature Protection](#), Navitas Semiconductor's third-gen GaNFast power ICs, How2Power Today, November 2021 issue.

[Semiconductor Supplier Adds SiC Diodes To Portfolio](#), Nexperia's PSC1065H (-J/-K/-L) 650-V, 10-A SiC Schottky diodes, How2Power Today, November 2021 issue.

[1200-V SiC Half-Bridge Power Modules Target Avionics Applications](#), Solitron Devices' SD11900 SiC Power Modules, How2Power Today, October 2021 issue.

[GaN Gate Driver Boosts Speed, Flexibility In Industrial And Home Automation](#), STMicroelectronics' STDRIVEG600 half-bridge gate driver, How2Power Today, October 2021 issue.

[750-V SiC FETs Boast A Low On-Resistance Of 6 mΩ](#), United SiC's Gen 4 750-V SiC FETs, How2Power Today, September 2021 issue.

[650-V GaN FET Features Integrated Driver And Enhanced Protection](#), Tagore Technology's TP44200NM 180-mΩ 650-V GaN E-HEMT device, How2Power Today, August 2021 issue.

[MOSFET Dies, Discretes And Power Modules Are Offered With 1700-V Rating](#), Microchip Technology's expanded SiC portfolio, How2Power Today, August 2021 issue.

[Bus Converter Reference Design Packs 1 kW Into Eighth-Brick Footprint](#), Efficient Power Conversions' EPC9149 reference design and demo board, How2Power Today, July 2021 issue.

[Totem-Pole PFC Controller Provides High Performance, Cost Effective Design](#), ON Semiconductor's NCP1680 CrM PFC controller IC, How2Power Today, July 2021 issue.

[650-V SiC Schottky Diodes Feature Low Built-In Voltage For High Efficiency](#), GeneSiC Semiconductor's fifth-generation GE*** series SiC Schottky MPS rectifiers, How2Power Today, July 2021 issue.

[150-V GaN HEMTs Raise Gate Withstand Voltage To 8 V](#), ROHM Semiconductor's 150-V GaN HEMT devices, How2Power Today, July 2021 issue.

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[GaN-Based Reference Design Demonstrates Heatsink-Free 250-W Resonant Converter](#), How2Power Today, June 2021 issue.

[Inverter Eval System Shows >99% Efficiency At 100 kHz Using SiC MOSFETs](#), Pre-Switch's CleanWave200 inverter evaluation system, How2Power Today, May 2021 issue.

[Intelligent SiC Power Modules For E-Mobility And Aerospace Applications](#), CISSOID's Three-Phase SiC MOSFET IPMs, How2Power Today, May 2021 issue.

[Easy-To-Design-In Gate Drivers Offer Reinforced Isolation](#), Infineon Technologies' EiceDRIVER X3 gate driver families, How2Power Today, May 2021 issue.

[Isolated Gate Driver Safely Controls SiC MOSFETs](#), STMicroelectronics' STGAP2SiCS STGAP family of isolated gate drivers, How2Power Today, May 2021 issue.

[Second-Generation 650-V GaN FETs Are Available In High Volume](#), Nexperia's GAN041-650WSB GaN FETs, How2Power Today, May 2021 issue.

[Design Tool Helps Identify Optimal SiC FET Design Solutions](#), UnitedSiC's FET-Jet Calculator, How2Power Today, April 2021 issue.

[Laser Driver IC Could Spur Burst Of Activity In Lidar Applications](#), Efficient Power Conversion's EPC21601 GaN-based laser driver IC, How2Power Today, March 2021 issue.

[Third-Gen SiC MOSFETs Boast Better Figures-of-Merit](#), GeneSiC Semiconductor's 1200-V G3R SiC MOSFETs, How2Power Today, March 2021 issue.

[Isolated Gate Driver Board Drives And Protects The Latest SiC Power Modules](#), Silicon Labs' Si823Hx gate driver board, How2Power Today, March 2021 issue.

[NSREC Notes: Space Power Components Answer Calls For Higher Performance, Lower Cost](#), mentions Renesas's Intersil ISL73033SEH low-side driver and 100-V GaN FET and Apogee Semiconductor's AFP1422 radiation-hardened PWM controller for GaN power switches, How2Power Today, March 2021 issue.

[Next-Gen SiC MOSFETs Are Optimized For xEVs And Industrial Applications](#), Rohm Semiconductor's 4G SiC MOSFETs, How2Power Today, February 2021 issue.

[High-Voltage Probe Measures SiC- And GaN-Based Power Converters](#), Teledyne LeCroy's HVD3220 high-voltage differential probe, How2Power Today, February 2021 issue.

[24-V Dual-Channel Gate Driver For Large Power Switches](#), Infineon Technologies' 2ED24427N01F low-side gate driver with an integrated thermal pad, How2Power Today, February 2021 issue.

[A Versatile Platform To Evaluate GaN Drivers And Transistors](#), GaN Systems's GS-EVB-HB-66508B-RN and GS-EVB-HB-66516T-RN 650-V half-bridge daughter cards, How2Power Today, February 2021 issue.

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[GaN Power Stage Enables 300-W Bidirectional Sixteenth Brick](#), Efficient Power Conversion's EPC9151 evaluation power module, How2Power Today, January 2021 issue.

[3300-V And 1700-V SiC MOSFETs Shrink Auxiliary Power Supplies](#), GeneSiC Semiconductor's 3300-V and 1700-V SiC MOSFETs, How2Power Today, January 2021 issue.

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[Transfer Molded IPM Brings SiC Advantages To 1200-V Modules](#), Infineon Technologies' CIPOS Maxi IPM 1200-V SiC integrated power module, How2Power Today, December 2020 issue.

[SiC Schottky Diodes Boast Surge Current Robustness](#), UnitedSiC's UJ3D1725K2, UJ3D1210K2, UJ3D1220K2 and UJ3D1250K2 1200-V and 1700-V SiC Schottkys, How2Power Today, December 2020 issue.

[Isolated IGBT/SiC MOSFET Gate Driver Benefits HEV/EV Applications](#), Texas Instruments' UCC5870-Q1 IGBT/SiC MOSFET gate driver, How2Power Today, November 2020 issue.

[6.5-kV SiC MOSFETs Offer High Performance For Medium-Voltage Applications](#), GeneSiC Semiconductor's 6.5-kV SiC MOSFET bare chips, How2Power Today, November 2020 issue.

[Next-Gen 650-V GaN Transistor Is Automotive Qualified](#), GaN Systems' GS-065-060-5-T-A 650-V, 60-A GaN transistor, How2Power Today, November 2020 issue.

[Automotive GaN FET Includes Driver, Protection And Active Power Management](#), Texas Instruments' LMG3522R030-Q1, LMG3525R030-Q1, LMG3422R050, LMG3425R050, LMG3422R030 and LMG3425R030 600-V and 650-V GaN FETs with integrated driver, protection and temperature reporting, How2Power Today, November 2020 issue.

[Efficient GaN-Powered LED Drivers Target Smart-Lighting Designs](#), Power Integrations' LYT6078C LED driver IC, How2Power Today, October 2020 issue.

[Rad Hard GaN Power Transistors Span 40 V To 300 V](#), EPC Space's rad hard GaN power transistors, How2Power Today, October 2020 issue.

[Devices Copackage Silicon Half-Bridge Driver And 650-V GaN Transistors](#), STMicroelectronics' MasterGaN1 GaN half bridge with integrated drivers, How2Power Today, October 2020 issue.

[100-V GaN FETs Feature Lower On-Resistance, Higher Voltage Ratings](#), Efficient Power Conversion's EPC2218 and EPC2204 100-V eGaN FETs

[SiC Power Module And Gate Driver Kit Speeds Inverter Design](#), Microchip Technology's AgileSwitch digital programmable gate driver and SP6LI SiC power module kit, How2Power Today, September 2020 issue.

[Latest Generation 200-V GaN FETs Double The Performance](#), EPC's EPC2215 and EPC2207 200-V eGaN FETs, How2Power Today, September 2020 issue.

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[SiC-Based Three-Phase Driver Module Delivers 80 A Peak, Is Fully Integrated](#), Apex Microtechnology's SA310 three-phase driver, How2Power Today, July 2020 issue.

[Second-Gen Technology Boosts Performance Of 650-V GaN FET Devices](#), Nexperia's GAN041-650WSB and GAN039-650NTB/NBB GaN FETs, How2Power Today, June 2020 issue.

[1200-V SiC MOSFETs Feature Low Gate Resistance For High Efficiency](#), Alpha and Omega Semiconductor's 1200-V SiC MOSFET platform which includes the AOK065V120X2 65-m Ω SiC MOSFET, How2Power Today, June 2020 issue.

[GaN Power Switch Increases Output Of Display PSUs To 75 W](#), Power Integrations' InnoSwitch3-MX isolated switcher IC family, How2Power Today, May 2020 issue.

[What We Missed At APEC: Silicon Carbide Marches On And Other Power Product News](#), Power Integrations' PowiGaN and SiC SCALE iDriver gate driver; ON Semiconductor's 1200-V and 900-V n-channel SiC MOSFETs including the 80-m Ω NVHL080N120SC1 and the NTB060N090SC1; Texas Instruments' 600-V GaN FETs with on-resistances of 150 m Ω , 70 m Ω , and 50 m Ω ; Efficient Power Conversion's EPC2152 80-V, 12.5-A power stage IC (driver plus eGaN FET half-bridge) and the EPC9148 GaN-based multi-level converter reference design; How2Power Today, April 2020 issue.

[650-V SiC MOSFETs Offer High Reliability And Performance](#), Infineon Technologies' 650-V CoolSiC MOSFETs, How2Power Today, April 2020 issue.

[650-V MOSFETs Expand SiC Benefits To Broader Range Of Industrial Applications](#), Cree's Wolfspeed C3M0015065D, C3M0015065K, C3M0060065D, C3M0060065J and C3M0060065K 650-V SiC MOSFETs, How2Power Today, April 2020 issue.

[Time-Of-Flight Demo Board Showcases GaN Speed In Driving Lasers](#), Efficient Power Conversion's EPC9144 laser diode driver demo board, How2Power Today, March 2020 issue.

[Robust Gate Drivers For Fast Switching SiC Power Modules](#), CISSOID's CMT-TIT0697 gate drivers for Wolfspeed's XM3 SiC MOSFET power modules, How2Power Today, February 2020 issue.

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[1200-V Enhancement-Mode GaN Power Devices Challenge SiC](#), GaN Power International's GPIHV15DK and GPIHV30DDP5L GaN power FETs, How2Power Today, December 2019 issue.

[GaN Power Transistors Target High-End Audio And SMPSs](#), Infineon Technologies' IGT40R070D1 E8220 and IGLD60R190D1 CoolGaN power transistors, How2Power Today, December 2019 issue.

[SiC FETs Lower On-Resistance To Less Than 10 m \$\Omega\$](#) , UnitedSiC's UF3SC SiC FETs, How2Power Today, December 2019 issue.

[Eval Board Paves Way For SiC MOSFETs In Motor Drives](#), Infineon Technologies' EVAL-M5-E1B1245N-SiC evaluation board, How2Power Today, November 2019 issue.

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[Half-Bridge Eval Board Demonstrates Benefits Of 650-V GaN HEMTs](#), GaN Systems' half-bridge GaN daughter board using GaN Systems' 650-V, 30-A GaN E-HEMTs and ON Semiconductor's NCP51820 high-speed gate-driver, How2Power Today, November 2019 issue.

[Offline Switcher ICs Adopt GaN For Higher Power Output And Efficiency](#), Power Integrations' INN3X79C and INN3X70C offline switcher ICs, How2Power Today, August 2019 issue.

[Sintered-Silver Packaging Technology Enhances Performance Of 650-V SiC FETs](#), UnitedSiC's two new TO220-3L package options for the UF3C FAST series of 650-V SiC FETs, How2Power Today, August 2019 issue.

[Gate-Driver System Works With 1.7-kV To 4.5-kV IGBT And SiC Power Modules](#), Power Integrations SCALE-iFlex gate-driver system, How2Power Today, July 2019 issue.

[900-V GaN-on-Si FETs Empower Three-Phase Industrial Power Supplies And Automotive Converters](#), Transphorm's Gen III TP90H050WS FET, How2Power Today, July 2019 issue.

[700-V MOSFETs And Schottkys Extend SiC Options For Designers](#), Microchip Technology's 700-V SiC MOSFETs and 700-V and 1200-V SiC Schottky barrier diodes, How2Power Today, June 2019 issue.

[AC-DC Converter ICs Add Built-In 1700-V SiC MOSFET For More Compact Designs](#), ROHM Semiconductor's BM2SCQ12xT-LBZ series ac-dc converter ICs, How2Power Today, May 2019 issue.

[Adapter Reference Design Leverages GaN-Based, Active-Clamp Flyback To Achieve High Density](#), Navitas's NVE039 27-W ac adapter reference design, How2Power Today, May 2019 issue.

[Rad-Tolerant PWM Controller And GaN FET Driver Come In Plastic Packages For SmallSats](#), Renesas Electronics' ISL71043M PWM controller and ISL71040M GaN FET driver, How2Power Today, May 2019 issue.

[Isolated Gate Drivers Integrate Sensing For IGBTs And SiC MOSFETs](#), Texas Instruments' UCC21710-Q1, UCC21732-Q1 and UCC21750 isolated gate drivers, How2Power Today, May 2019 issue.

[SJ MOSFETs Offer Fast Reverse Recovery And Design Flexibility For EV Charging Stations, Home Appliances](#), ROHM Semiconductor's R60xxJNx 600-V superjunction MOSFETs, How2Power Today, May 2019 issue.

[Automotive-Qualified GaN FET Improves Lidar System Resolution](#), EPC's 80-V EPC2214 eGaN FET, How2Power Today, May 2019 issue.

[Large Portfolio Of Automotive-Grade SiC MOSFETs For EV Applications](#), Rohm Semiconductor's SCT3xxxxHR series SiC MOSFETs, How2Power Today, April 2019 issue.

[SiC-MOSFET Gate Driver Improves Efficiency And Safety](#), Power Integrations' SIC1182K SCALE-iDriver SiC-MOSFET gate driver, How2Power Today, March 2019 issue.

[AEC-Qualified GaN FETs For Lidar And 48-V Power Systems](#), EPC's EPC2206 and EPC2212 eGaN devices, How2Power Today, February 2019 issue.

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[600-V GaN FET Power Stages Boost Performance For Applications Up To 10 kW](#), Texas Instruments' LMG34x family of 600-V GaN power stages, How2Power Today, November 2018 issue.

[SiC FETs Offer Faster Switching With Cascode Convenience](#), UnitedSiC's UF3C FAST series 650-V and 1200-V SiC FETs, How2Power Today, November 2018 issue.

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[Gate Driver Core Is Optimized For SiC MOSFET Modules](#), AgileSwitch's ASC1 SiC MOSFET gate driver core, How2Power Today, July 2018 issue.

[SiC Schottky Diodes Are Tailored For On-Board Chargers In Hybrids And EVs](#), Infineon Technologies' CoolSiC Schottky diode family, How2Power Today, June 2018 issue.

[SiC JFET Cascodes Are High-Performance Upgrades For IGBTs And MOSFETs](#), UnitedSiC's UJ3C1200 series of 1200-V SiC JFET cascodes, How2Power Today, June 2018 issue.

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[1200-V SiC MOSFETs Offer 120-m \$\Omega\$ or 160-m \$\Omega\$ On-Resistance, Littelfuse and Monolith Semiconductor's LSIC1MO120E0120 and LSIC1MO120E0160 SiC MOSFETs](#), How2Power Today, March 2018 issue.

[Rad-Hard GaN Devices Propel Space Power Supplies To Higher Performance](#), Renesas Electronics' ISL7002xSEH GaN FETs and ISL70040SEH GaN FET driver, How2Power Today, February 2018 issue.

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[SJ MOSFETs Are Optimized For High-Power Soft-Switching Topologies](#), Infineon Technologies' CoolMOS CFD7 family of SJ MOSFETs, How2Power Today, December 2017 issue.

[Power Electronics Simulator Adds Support For SiC & GaN Modules And More](#), Powersim's PSIM simulator, version 11.1, How2Power Today, December 2017 issue.

[GaN Eval Board Simplifies MegaHertz Power For Audio And Other Applications](#), GaN Systems' GS61004B-EVBDC evaluation board, How2Power Today, November 2017 issue.

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[GaN-Based Inverter Reference Design Raises Performance For AC Servo Drives](#), Texas Instruments' three-phase, GaN-based inverter reference design, How2Power Today, August 2017 issue.

[GaN Power ICs Enable Smallest Power Adapters For Ultra-Thin TVs And Laptops](#), Navitas Semiconductor's 150-W ac-dc reference design using GaN power ICs, How2Power Today, July 2017 issue.

[1200-V SiC Diodes Improve Performance Of Appliances, Vehicle Chargers](#), STMicroelectronics' 1200-V SiC Schottky diodes, How2Power Today, June 2017 issue.

[GaN FETs Meet Hybrid, Electric Vehicle Needs](#), Transphorm's TPH3205WSBQ 650-V GaN FET, How2Power Today, May 2017 issue.

[GaN Power ICs Enter The Market](#), Navitas Semiconductor's NV6131, NV6105 and NV6115 iDrive GaN power ICs, How2Power Today, February 2017 issue.

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[High-Voltage Scope Probe Measures Fastest GaN Power Switches](#), Picotest.com's P2000A high-voltage gallium nitride (GaN) voltage probe, How2Power Today, December 2016 issue.

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[Comprehensive Platform Eases Evaluation Of GaN Transistors](#), GaN Systems' daughterboard-style evaluation kit, How2Power Today, November 2016 issue.

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[Monolithic GaN ICs Integrate 650-V Half Bridge With Gate Drivers And Logic](#), Dialog Semiconductor's DA8801 GaN ICs, How2Power Today, September 2016 issue.

[1700-V SiC MOSFET Reduces Losses In Industrial Applications](#), ROHM's SCT2H12NZ SiC MOSFET, How2Power Today, August 2016 issue.

[Speedy FET Driver Unleashes GaN Performance](#), Peregrine Semiconductor's PE29100 GaN FET driver, How2Power Today, August 2016 issue.

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[1200-V SiC MOSFETs Deliver Dramatic Improvements Versus Silicon IGBTs](#), Infineon's CoolSiC MOSFETs and modules, How2Power Today, May 2016 issue.

[Embedded Component Packaging Leads To Tiny GaN Transistors](#), AT&S's Embedded Component Technology, How2Power Today, May 2016 issue.

[GaN Power ICs Integrate Power FET With Gate Drive And Logic](#), Navitas Semiconductor's 650-V GaN Power ICs, How2Power Today, April 2016 issue.

[650-V GaN FET Delivers Low On-Resistance In TO-247](#), Transphorm's TPH3207WS GaN FET, How2Power Today, April 2016 issue.

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[High-Temp SiC Power Modules Offer Different Configurations, Current Ratings](#), CISSOID's CHT-PLUTO and CHT-EUROPA SiC power modules, How2Power Today, December 2015 issue.

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[900-V SiC MOSFET Outperforms Superjunction Silicon MOSFETs](#), Cree's C3M0065090J SiC MOSFET, How2Power Today, July 2015 issue.

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[GaN Transistors Are Cheaper Than Silicon](#), Efficient Power Conversion's EPC2035 and EPC2036 eGaN power transistors, How2Power Today, May 2015 issue.

[Top Five Products And Demos Seen at APEC 2015](#), features Efficient Power Conversion's EPC9115 500-W eighth-brick demo design using the company's eGaN FETs and Cree's SiC-module-based 50-kW string PV inverter demo, How2Power Today, April 2015 issue.

[GaN FETs + Driver Module Lowers Barriers To GaN-Based Power Design](#), Texas Instruments' LMG5200 80-V 10-A GaN FET half-bridge power stage, How2Power Today, March 2015 issue.

[SiC MOSFETs Miniaturize Ultra-High Voltage Pulse Generators](#), Rohm Semiconductor's SCT2080KE SiC MOSFET, How2Power Today, March 2015 issue.

[1200-V SiC MOSFET Features <290 mΩ On-Resistance To 200°C](#), STMicroelectronics' SCT20N120 1200-V SiC power MOSFET, How2Power Today, February 2015 issue.



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2014:

[1200-V And 1700-V SiC Junction Transistors Are Positioned To Challenge SiC MOSFETs And Silicon IGBTs](#), GeneSiC Semiconductor's 1700-V and 1200-V SiC junction transistors, How2Power Today, November 2014 issue.

[All-SiC Half-bridge Module Reduces Cost And Size For Inverters](#), Cree's CAS300M17BM2 all-SiC 1.7-kV half-bridge power module, How2Power Today, October 2014 issue.

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[100-V eGaN FET Benefits Power Switching And RF Applications](#), Efficient Power Conversion's EPC8010 100-V eGaN FET, How2Power Today, March 2014 issue.

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[Development Board Facilitates Design of High-Frequency Converters Using GaN Transistors](#), Efficient Power Conversion's EPC9010 development board for 100-V eGaN FETs, How2Power Today, April 2013 issue.

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2012:

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[GaN-on-Si Based FETs Foster New Applications](#), Efficient Power Conversion's EPC1005, EPC1014 and EPC1015 eGaN FETs, How2Power Today, December 2012 issue.

[As All-SiC Module Emerges, GaN Powers Server Supplies](#); Cree's CAS100H12AM1 1200-V SiC module, Fairchild Semiconductor's 1200-V SiC BJTs and related discrete driver boards and reference designs, and Microsemi's APT10SCD120BCT, APT20SCD120B, APT30SCD120B, APT20SCD120S, and APT30SCD120S 1200-V SiC Schottky diodes; How2Power Today, November 2012 issue.

[Development Boards Simplify Evaluation Of eGAN FETs](#), Efficient Power Conversion's EPC9003 and EPC9006 output power stages with 100-V or 200-V eGAN FETs in half-bridge plus driver IC, How2Power Today, October 2012 issue.

[Is Silicon Carbide Technology Ready To Take Off?](#), Cree's CMF20120D 1200-V SiC MOSFET, Fairchild Semiconductor's 1200-V SiC BJTs, STMicroelectronics' 650-V SiC Schottky diodes, and Infineon's 650-V thinQ! SiC Schottky diodes; How2Power Today, October 2012 issue.

[High-Voltage GaN HEMT Achieves JEDEC Qualification](#), Transphorm's TPH2006PS 600-V GaN HEMT, How2Power Today, September 2012 issue.

[50-A Power Devices Extend SiC Benefits To More Applications](#), Cree's CPM2-1700-0040B 1700-V SiC MOSFET, CPM2-1200-0025B 1200-V SiC MOSFET and 1700-V, 1200-V, and 650-V SiC Schottky diodes; How2Power Today, May 2012 issue.

[650-V 55-mΩ SiC JFETs Boast Extremely Low On-Resistance](#), SemiSouth Laboratories' SJDA065R055 650-V SiC JFETs, How2Power Today, May 2012 issue.

[RFMD Leverages RF GaN Capability To Build Power HEMTs](#), RF Micro Devices' RFJS1506F and RFJS3006F 650-V GaN HEMTs, How2Power Today, May 2012 issue.

[As GaN Power Preps For Production, More Suppliers Enter The Fray](#), How2Power Today, March 2012 issue.

[Gate Drivers Work With Silicon Or GaN FETs](#), Texas Instruments' LM5114 low-side gate driver, How2Power Today, February 2012 issue.

[Demo Suggests Cascode MOSFET Stacks up Well Against SiC And Si Switches](#), From Alpha and Omega Semiconductor and SemiSouth Laboratories, a jointly demonstrated UniSiC 1200-V, 90-mΩ MOSFET; How2Power Today, January 2012 issue.

[Compound Power Devices Co-Package SiC Schottkys With MOSFETs Or IGBTs](#), Renesas Electronics' RJQ6020DPM, RJQ6021DPM and RJQ6022DPM 600-V SiC compound power devices, How2Power Today, January 2012 issue.

[600-V SiC Schottky Targets Air Conditioners, Base Stations, And Solar Arrays](#), Renesas Electronics' RJS6005TDPP 600-V rated SiC Schottky barrier diode, How2Power Today, January 2012 issue.

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1200-V/5-A SiC Diodes Come In DPAK Packaging, SemiSouth Laboratories' SDB05S120 1200-V SiC diodes, story appears in [Power Product Roundup: Diodes And Rectifiers](#), How2Power Today, October 2011 issue.

SiC Schottkys In DPAKs Offer 2-A To 10-A Ratings, Cree's C4D02120E, C4D05120E, C4D08120E, and C4D10120E series 1200-V SiC Schottky diodes; story appears in [Power Product Roundup: Diodes And Rectifiers](#), How2Power Today, October 2011 issue.

1200-V SiC JFET Power Module Is Offered As Standard Product, Microsemi's APTJC120AM13VCT1AG 1200-V SiC power module, story appears in [Power Product Roundup: Power MOSFETs , IGBTs, And Modules](#), How2Power Today, September 2011 issue.

1200-V SiC JFET Delivers Low On-Resistance, SemiSouth Laboratories' SJDP120R045 and SJDC120R045 1200-V SiC JFETs, story appears in [Power Product Roundup: Power MOSFETs, IGBTs, And Modules](#), How2Power Today, September 2011 issue.

Second-Gen 200-V GaN Transistor Delivers Enhanced Performance, Efficient Power Conversion's EPC2010 200-V eGaN FET, story appears in [Power Product Roundup: Power MOSFETs , IGBTs, And Modules](#), How2Power Today, September 2011 issue.

Development Board Eases Designs Based On 100-V GaN FETs, Efficient Power Conversion's EPC9006 development board for EPC2007 100-V eGaN FET, story appears in [Power Product Roundup: Power MOSFETs, IGBTs, And Modules](#), How2Power Today, September 2011 issue.

SiC JFETs Target High-end Audio, SemiSouth Laboratories' SJEP120R100A and SJEP120R063A SiC JFETs, story appears in [High-Temperature Components For Power Design](#), How2Power Today, August 2011 issue.

1200-V SiC Schottkys Offer Higher Performance At Lower Cost, Cree's C4D02120x, C4D05120x, C4D10120x, C4D20120x, and C4D40120x 1200-V SiC Schottky diodes; story appears in [High-Temperature Components For Power Design](#), How2Power Today, August 2011 issue.

[Dedicated Driver Squeezes Optimal Performance Out Of eGaN FETs](#), National Semiconductor's LM5113 100-V half-bridge driver for eGaN FETs, How2Power Today, June 2011 issue.

[Lower Current Rating And Price Extends SiC MOSFET Benefits To More Apps](#), Cree's CMF10120D 1200-V SiC MOSFET, How2Power Today, May 2011 issue.

[GaN Transistors Make Inroads Commercially While Technology Expands To Higher Voltages](#), Efficient Power Conversion's eGaN FETs, Transphorm's 600-V GaN diode and International Rectifier's iP2010/11 GaN-on-Si buck converter power stage; How2Power Today, May 2011 issue.

[Emerging High-Voltage Apps Accelerate Silicon Carbide Growth](#); Cree's CMF20120D SiC MOSFET, SemiSouth Laboratories' SJEP120R100, SJEP120R063 and SJEP170R550 SiC JFETs, GeneSiC's 6.5-kV SiC SCR-mode thyristors, ROHM Semiconductor's SCS1xxAGC Schottky diodes, and Fairchild/TranSiC's 1200-V SiC BJTs; How2Power Today, April 2011 issue.

[GaN Semiconductor Startup Demos 99% Efficient DC-DC Boost Converter](#), Transphorm's 400-W PFC boost converter demo, How2Power Today, March 2011 issue.



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[Second-Gen GaN Transistors Feature Enhanced Performance, Lead-Free Packaging](#), Efficient Power Conversion's EPC2001 100-V eGaN FET and EPC2015 40-V eGaN FET, How2Power Today, March 2011 issue.

[Surface-Mount SiC Schottky Targets Solar Micro-inverters](#), Cree's C2D05120 1200-V SiC Schottky diode, How2Power Today, February 2011 issue.

[SiC JFETs Are Now Shipping in Commercial Quantities](#), SemiSouth Laboratories' SJEP120R100, SJEP120R063, SJEP120R085 and SJEP170R550 1200-V and 1700-V SiC JFETs, How2Power Today, February 2011 issue.

[1200-V Silicon Carbide MOSFET Aims To Replace Silicon Devices](#), Cree's CMF20120D 1200-V SiC MOSFET, How2Power Today, January 2011 issue.

[SiC Schottkys Support Power Supply Designs for More-Efficient Data Centers](#), Cree's C3DXX065A series 650-V SiC Schottky diodes, How2Power Today, January 2011 issue.

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[1200-V SiC Schottky Family Features 30-A Device In TO-247](#), SemiSouth Laboratories' family of 1200-V SiC Schottky diodes including part number SDP30S120, How2Power Today, November 2010 issue.

[High-Temperature Controller And Driver Improve Performance Of SiC Switches](#), Cissoid's Themis controller and Atlas push-pull driver stage for SiC MOSFETs and JFETs, How2Power Today, November 2010 issue.

[SiC Schottkys Push Voltage Ratings to 1700 V](#), Cree's CPW3-1700S010B and CPW3-1700S025B 1700-V SiC Schottky diodes, How2Power Today, April 2010 issue.

[GaN Power Transistors Seek To Replace Silicon Power MOSFETs](#), Efficient Power Conversion's EPC 1014, 1015, 1009, 1005, 1007, 1001, 1013, 1011, 1012, and 1010 40-V to 200-V eGaN FETs; How2Power Today, March 2010 issue.

[GaN-Based Power Stages Look To Reshape Point-of-Load Landscape](#), International Rectifier's GaN iP2010 and iP2011 integrated power stages, How2Power Today, March 2010 issue.

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[Dual SiC MOSFET Modules Promise High Efficiency](#), Powerex's QJD1210006 and QJD1210007 1200-V SiC MOSFET modules, How2Power Today, November 2009 issue.